



2SKTJ04

JFET

FIELD EFFECT TRANSISTOR SILICON N-CHANNEL JUNCTION TYPE

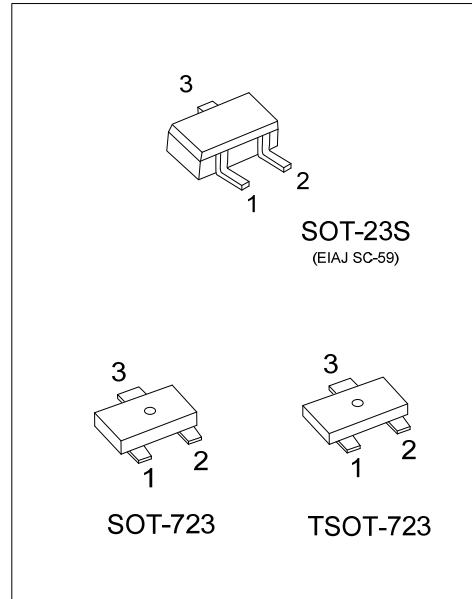
DESCRIPTION

The UTC **2SKTJ04** is an N-channel junction silicon FET, it uses UTC's advanced technology to provide the customers with low I_{DSS} and low C_{RSS} .

The UTC **2SKTJ04** is suitable for audio frequency low noise amplifier, impedance conversion, infrared sensor applications.

FEATURES

* Breakdown voltage: $V_{DGO}=20V$



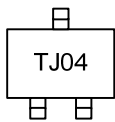
ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
2SKTJ04L-x-AE3S-R	2SKTJ04G-x-AE3S-R	SOT-23S	D	S	G	Tape Reel
2SKTJ04L-x-AH7-R	2SKTJ04G-x-AH7-R	TSOT-723	D	S	G	Tape Reel
2SKTJ04L-x-AQ3-R	2SKTJ04G-x-AQ3-R	SOT-723	D	S	G	Tape Reel

Note: Pin Assignment: D: Drain S: Source G: Gate

<p>2SKTJ04G-x-AE3S-R</p> <p>(1) Packing Type (2) Package Type (3) Rank (4) Green Package</p>	<p>(1) R: Tape Reel (2) AE3S: SOT-23S, AH7: TSOT-723, AQ3: SOT-723 (3) x: refer to CLASSIFICATION OF I_{DSS} (4) G: Halogen Free and Lead Free, L: Lead Free</p>
--	---

MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage (Gate Open)	V _{DSO}	20	V
Drain-Gate Voltage (Source Open)	V _{DGO}	20	V
Drain-Source Current (Gate Open)	I _{DSO}	2	mA
Drain-Gate Current (Source Open)	I _{DGO}	2	mA
Power Dissipation	P _D	100	mW
Operating Ambient temperature	T _{OPR}	-20 ~ +80	°C
Storage Temperature Range	T _{STG}	-55 ~ +125	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
Drain Current (Note 1)	I _D	V _{DD} =2.0V, R _D =2.2kΩ±1%	2SKTJ04-S	100		220	μA
			2SKTJ04-T	180		320	μA
			2SKTJ04-U	280		470	μA
Drain-Source Leakage Current	I _{DSS}	V _{DD} =2.0V, R _D =2.2kΩ±1%, V _{GS} =0V	110		460	μA	
Forward Transfer Admittance	y _{fs}	V _{DS} =2.0V, V _{GS} =0V, f=1kHz	660			μS	
Output Noise Voltage	V _{NO}	V _{DD} = 2V, C _g = 5pF, A-curve filter, R _L = 2.2kΩ		-102		dB	
Voltage gain	G _V	V _{DD} = 2V, R _L = 2.2kΩ, C _g = 5pF, f = 1kHz, V _{in} = 10mV		-1.0		dB	

Notes: 1. A protection diode is built-in between gate and source of transistor.

However if forward current flows between gate and source transistor might be damaged.

So please be careful not insert reverse.

2. I_D is assured for I_{DSS}.

■ CLASSIFICATION OF I_{DSS}

RANK	S	T	U
RANGE	110 ~ 210	190 ~ 310	290 ~ 460

UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. UTC reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.